Gas Cluster Ion Beam Equipment

*nFusion™ 500 Series*

Prof. Isao YAMADA (Kyoto University)

Characteristics & Applications of GCIB

- Ultra shallow doping
- Modification of surface structure & composition
- Co-incident doping of multiple species
- Atomic level surface smoothing
- Asperity removal
- Directional etching
- Assisted deposition of thin films

**Gas Cluster:**

- $(\text{Ar})_n$
- $(\text{O}_2)_n$
- $(\text{CO}_2)_n$
- $(\text{SF}_6)_n$
- $(\text{N}_2)_n$

$n \sim 2000$

Patent status & Patent owner contact

- Patent No.: USP5459326; 5814194; 6207282; 6797334; 6797339
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TEL EPION INC.

300mm Si Wafer